

# 3STR1630

## Low voltage high performance NPN power transistor

#### Features

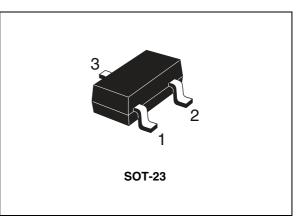
- Very low collector-emitter saturation voltage
- High current gain characteristic
- Fast switching speed
- Miniature SOT-23 plastic package ECOPACK<sup>®</sup>2 grade for surface mounting circuits

### **Applications**

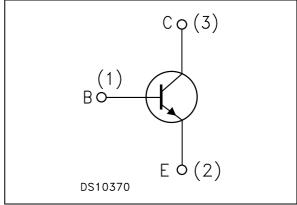
- Strobe and LED drives
- Motor and relay drives
- DC-DC converters

### Description

This device is an NPN transistor manufactured using low voltage planar technology with a double-metal process.







#### Table 1. Device summary

Order code	Marking	Package	Packing
3STR1630	1630	SOT-23	Tape and reel

## 1 Electrical ratings

Table 2.	Absolute n	naximum	ratinas
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Symbol	Parameter	Value	Unit			
V <sub>CES</sub>	Collector-emitter voltage (V <sub>BE</sub> = 0)	30	V			
V <sub>CEO</sub>	Collector-emitter voltage ( $I_B = 0$ )	30	V			
$V_{\text{EBO}}$	Emitter-base voltage ( $I_C = 0$ )	5	V			
۱ <sub>C</sub>	Collector current	6	Α			
I <sub>CM</sub>	Collector peak current (t <sub>P</sub> < 5 ms)	12	А			
P <sub>TOT</sub>	Total dissipation at T <sub>amb</sub> = 25 °C	0.5	W			
T <sub>STG</sub>	Storage temperature	-65 to 150	°C			
ТJ	Max. operating junction temperature	150	°C			

#### Table 3.Thermal data

Symbol	Parameter	Value	Unit
R <sub>thJA</sub> <sup>(1)</sup>	Thermal resistance junction-ambient max	250	°C/W

1. Device mounted on PCB area of 1 cm<sup>2</sup>.



## 2 Electrical characteristics

 $T_{case}$  = 25 °C unless otherwise specified.

Table 4. Electrical characteristics						
Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I <sub>CBO</sub>	Collector cut-off current $(I_E = 0)$	V <sub>CB</sub> = 30 V			0.1	μA
I <sub>EBO</sub>	Emitter cut-off current $(I_{\rm C} = 0)$	V <sub>EB</sub> = 4 V			0.1	μA
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage (I <sub>E</sub> = 0)	l <sub>C</sub> = 100 μA	30			V
V <sub>(BR)CEO</sub> <sup>(1)</sup>	Collector-emitter breakdown voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 10 mA	30			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage (I <sub>C</sub> = 0)	I <sub>E</sub> = 100 μA	5			V
V <sub>CE(sat)</sub> <sup>(1)</sup>	Collector-emitter saturation voltage			60 140 240	90 190 300	mV mV mV
V <sub>BE(sat)</sub> <sup>(1)</sup>	Base-emitter saturation voltage	$I_{C} = 2 A \qquad I_{B} = 40 \text{ mA}$ $I_{C} = 5 A \qquad I_{B} = 500 \text{ mA}$		830 1000	1100	mV mV
h <sub>FE</sub> <sup>(1)</sup>	DC current gain		210 180 170	260 90	560	
f <sub>t</sub>	Transition frequency	$I_{\rm C} = 0.1 \ {\rm A}$ $V_{\rm CE} = 10 \ {\rm V}$		100		MHz
C <sub>CBO</sub>	Collector-base capacitance (I <sub>E</sub> = 0)	V <sub>CB</sub> = 40 V, f = 1 MHz		15		pF
t <sub>on</sub> t <sub>off</sub>	Resistive load Turn-on time Turn-off time	$\begin{split} I_{C} &= 2.5 \text{ A} \qquad V_{CC} = 12 \text{ V} \\ I_{B1} &= -I_{B2} = 125 \text{ mA} \\ V_{BE(off)} &= -5 \text{ V} \end{split}$		90 450		ns ns

Table 4.	Electrical	characteristics

1. Pulse test: pulse duration  $\leq$ 300 µs, duty cycle  $\leq$ %

### 2.1 Electrical characteristics (curves)

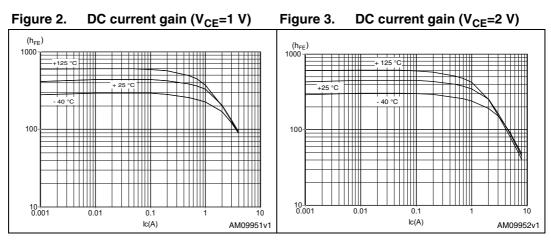


Figure 4. Collector-emitter saturation Figure 5. voltage (V<sub>CEsat</sub> @ h<sub>FE</sub>=10)

Collector-emitter saturation voltage (V<sub>CEsat</sub> @ h<sub>FE</sub>=50)

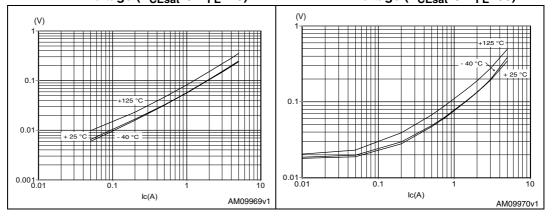
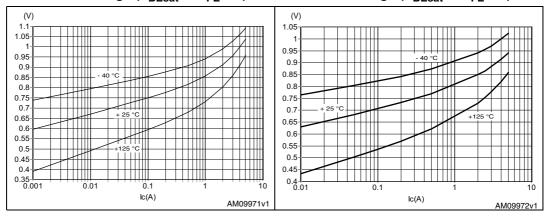


Figure 6. Base-emitter saturation voltage (V<sub>BEsat</sub> @ h<sub>FE</sub>=10)

Figure 7. Base-emitter saturation voltage (V<sub>BEsat</sub> @ h<sub>FE</sub>=50)





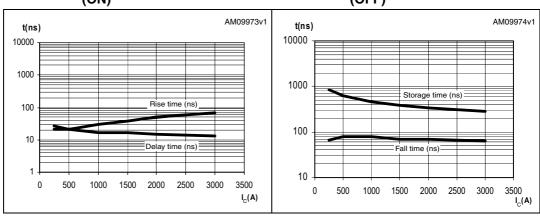
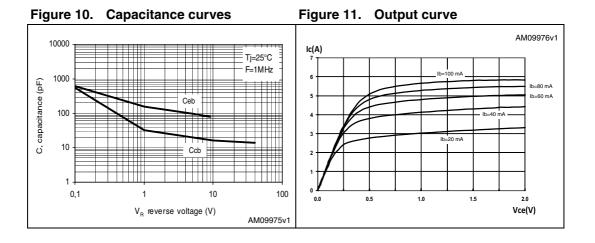


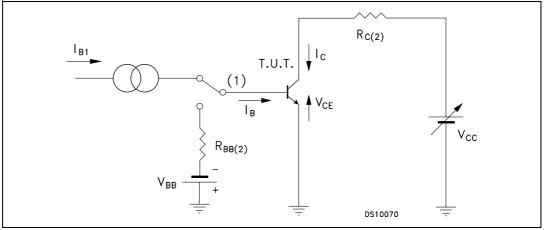
Figure 8. Resistive load switching time Figure 9. Resistive load switching time (ON) (OFF)





### 2.2 Test circuits





1. Fast electronic switch

2. Non-inductive resistor



## 3 Package mechanical data

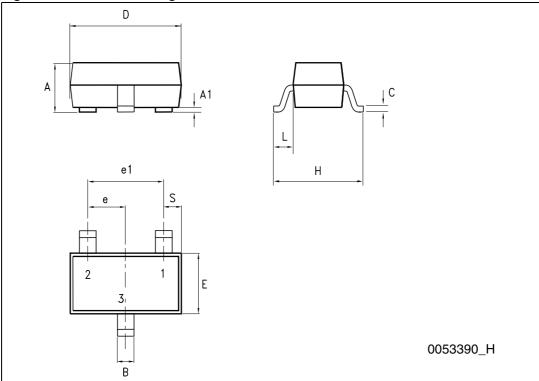
In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK<sup>®</sup> is an ST trademark.



Dim.	mm.			
Dini.	Min.	Тур.	Max.	
A	0.89		1.4	
A1	0		0.1	
В	0.3		0.51	
С	0.085		0.18	
D	2.75		3.04	
e	0.85		1.05	
e1	1.7		2.1	
E	1.2		1.6	
н	2.1		2.75	
L		0.6		
S	0.35		0.65	

 Table 5.
 SOT-23 mechanical data







## 4 Revision history

#### Table 6.Document revision history

Date	Revision	Changes
02-Nov-2009	1	Initial release
17-Jan-20112Removed "Preliminary data"		Removed "Preliminary data" text from coverpage header.
15-Jun-2011	3	Curves inserted Modified: <i>Table 4</i>



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